

General Description

The QM2403J is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The QM2403J meet the RoHS and Green Product requirement , with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 8	V
$I_D@T_A=25^{\circ}\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}^1$	-4.3	A
$I_D@T_A=70^{\circ}\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}^1$	-3.5	A
I_{DM}	Pulsed Drain Current ²	-17.2	A
$P_D@T_A=25^{\circ}\text{C}$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	85	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	30	$^{\circ}\text{C/W}$

Product Summary

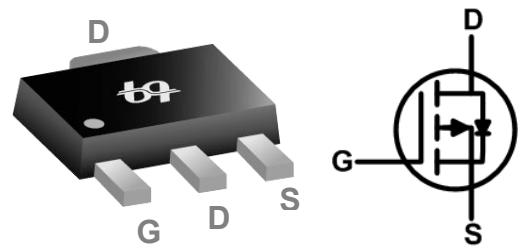


BVDSS	RDSON	ID
-20V	55mΩ	-4.3A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT89 Pin Configuration



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.016	---	V/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5V, I_D=-4A$	---	44	55	$\text{m}\Omega$
		$V_{GS}=-2.5V, I_D=-3A$	---	56	70	
		$V_{GS}=-1.8V, I_D=-2A$	---	73	85	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.3	-0.5	-1.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3.97	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-16V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-16V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-4A$	---	14.2	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-4A$	---	12.1	16.9	nC
Q_{gs}	Gate-Source Charge		---	1.72	2.4	
Q_{gd}	Gate-Drain Charge		---	3	4.2	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-10V, V_{GS}=-4.5V, R_G=3.3\Omega, I_D=-4A$	---	4.4	8.8	ns
T_r	Rise Time		---	50.6	91	
$T_{d(off)}$	Turn-Off Delay Time		---	45	90	
T_f	Fall Time		---	25	50	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	938	1313	pF
C_{oss}	Output Capacitance		---	108	151	
C_{rss}	Reverse Transfer Capacitance		---	96	134	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-4.3	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-17.2	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$IF=-4A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	25.7	---	nS
Q_{rr}	Reverse Recovery Charge		---	6.7	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

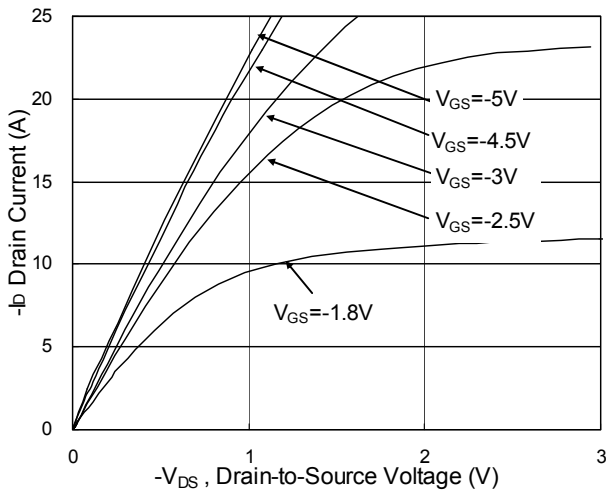


Fig.1 Typical Output Characteristics

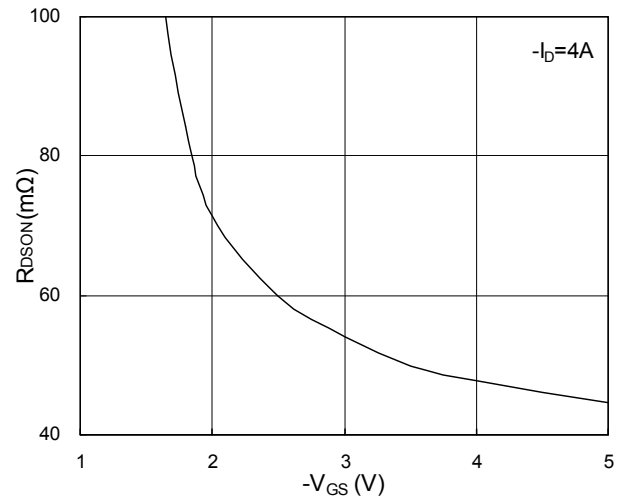


Fig.2 On-Resistance vs. G-S Voltage

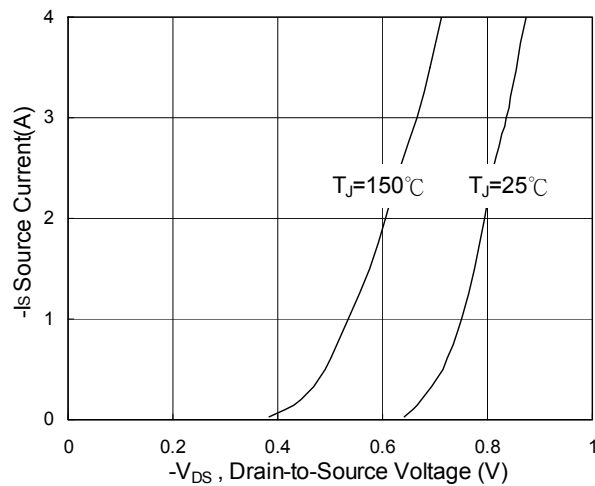


Fig.3 Forward Characteristics of Reverse

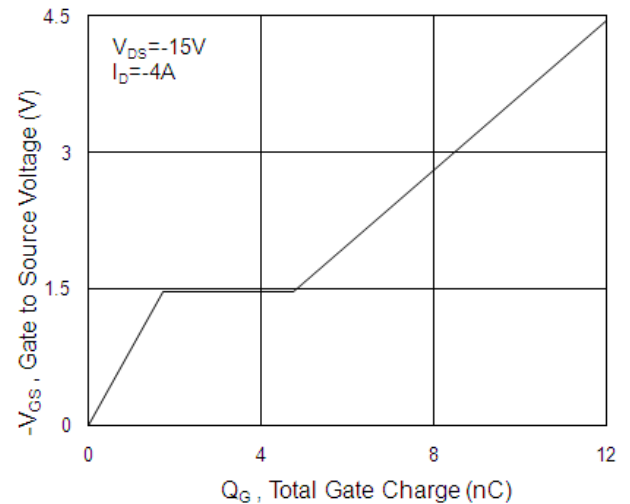


Fig.4 Gate-Charge Characteristics

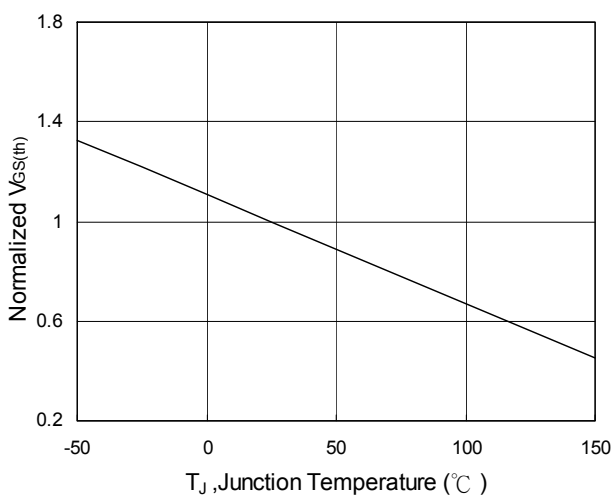


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

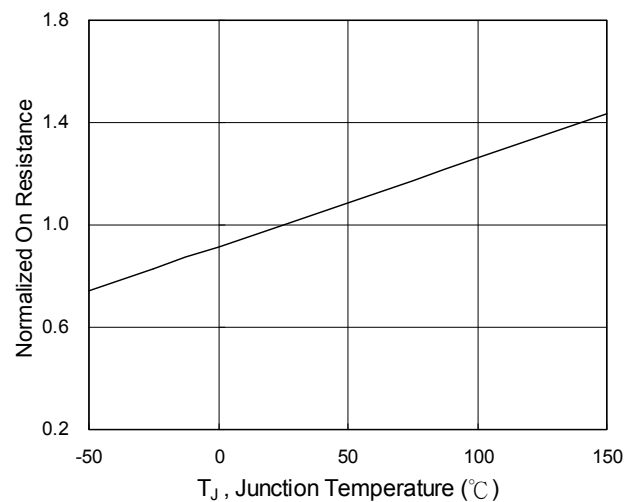


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

P-Ch 20V Fast Switching MOSFETs

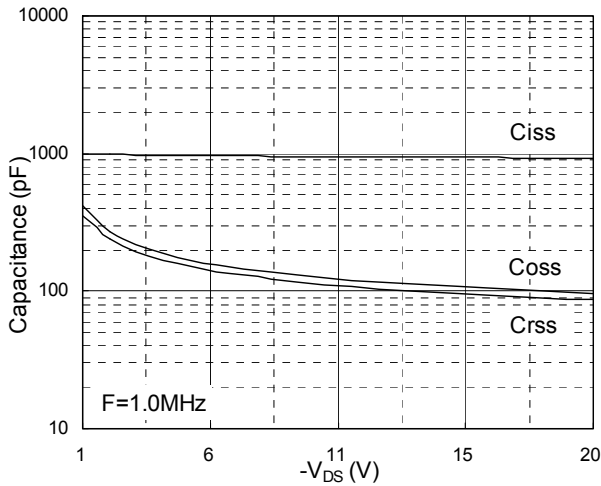


Fig.7 Capacitance

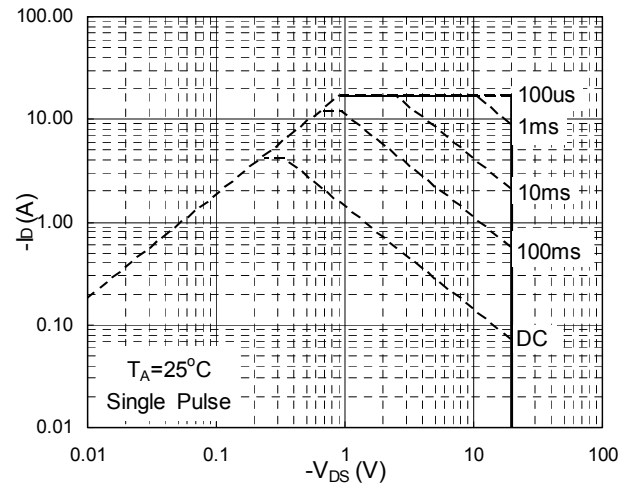


Fig.8 Safe Operating Area

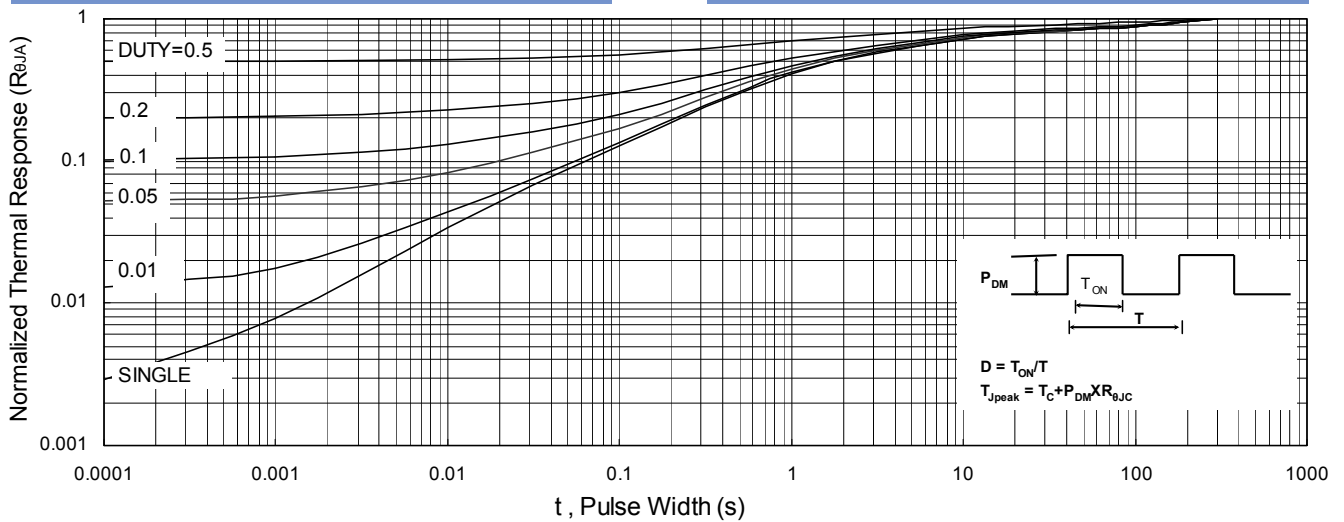


Fig.9 Normalized Maximum Transient Thermal Impedance

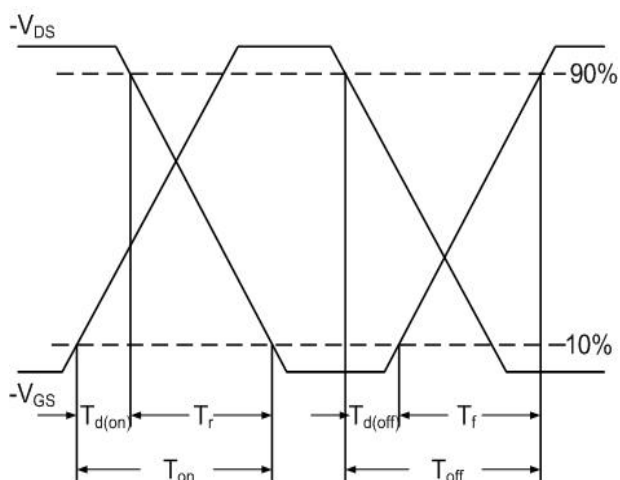


Fig.10 Switching Time Waveform

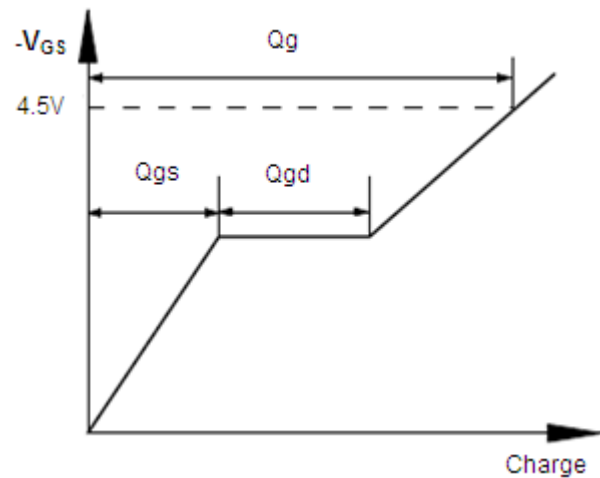


Fig.11 Gate Charge Waveform